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Power Matters™

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- ▶ Product Directory
- ▶ Applications Directory
- ▶ Parametric Search

Overview	Diagrams

Symbol	Min	Тур	Max	Unit
V _{CE(sat)}			2.00	V
HFE	50.00		200.00	
	V _{CE(sat)}	V _{CE(sat)}	V _{CE(sat)}	V _{CE(sat)} 2.00

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			120.00	V
Collector Current (dc)	I _C			7.00	А
Collector-Emitter Voltage (Base Open)	V_{CEO}			50.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			7.00	V
Power Dissipation, Total	P _T			35.00	W

This part can be found in the following product categories:

- → Discretes → Transistors → BJT(BiPolar Junction Transistor) → PNP Transistor

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